

# **Octal 3-STATE Transceiver** MM74HC245A

# **General Description**

The MM74HC245A 3-STATE bidirectional buffer utilizes advanced silicon-gate CMOS technology, and is intended for two-way asynchronous communication between data buses. It has high drive current outputs which enable high speed operation even when driving large bus capacitances. This circuit possesses the low power consumption and high noise immunity usually associated with CMOS circuitry, yet has speeds comparable to low power Schottky TTL circuits.

This device has an active LOW enable input G and a direction control input, DIR. When DIR is HIGH, data flows from the A inputs to the B outputs. When DIR is LOW, data flows from the B inputs to the A outputs. The MM74HC245A transfers true data from one bus to the other.

This device can drive up to 15 LS-TTL Loads, and does not have Schmitt trigger inputs. All inputs are protected from damage due to static discharge by diodes to VCC and ground.

#### **Features**

• Typical Propagation Delay: 13 ns

• Wide Power Supply Range: 2 V to 6 V

• Low Quiescent Current: 160 μA Maximum (74HC)

• 3-STATE Outputs for Connection to Bus Oriented Systems

• High Output Current: 6 mA (Minimum)

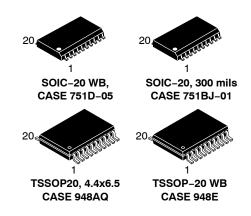
• Same as the 645

• These are Pb-Free Devices

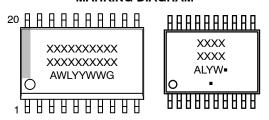
### **TRUTH TABLE**

Control Inputs		
G	DIR	Operation
L	L	B data to A bus
L	Н	A data to B bus
Н	Х	Isolation

NOTE: H = HIGH Level L = LOW Level X = Irrelevant



#### **MARKING DIAGRAM**



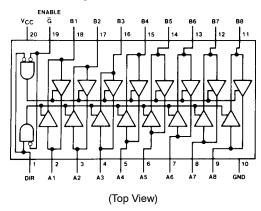
XXXXX = Specific Device Code = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

#### **CONNECTION DIAGRAM**

Pin Assignment for SOIC and TSSOP



# ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

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# **Logic Diagram**

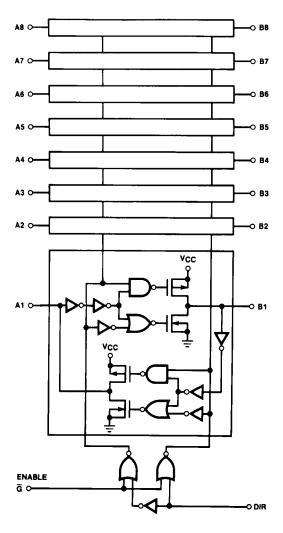


Figure 1. Logic Diagram

# ABSOLUTE MAXIMUM RATINGS (Note 1)

Symbol	Parameter	Rating	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7.0	V
V <sub>IN</sub>	DC Input Voltage DIR and G pins	-0.5 to V <sub>CC</sub> +0.5	V
V <sub>IN,</sub> V <sub>OUT</sub>	DC Input/Output Voltage	-0.5 to V <sub>CC</sub> +0.5	V
I <sub>CD</sub>	Clamp Diode Current	±20	mA
I <sub>OUT</sub>	DC Output Current, per pin	±35	mA
Icc	DC V <sub>CC</sub> or GND Current, per pin	±70	mA
T <sub>STG</sub>	Storage Temperature Range	-65 to +150	°C
$P_{D}$	Power Dissipation (Note 2)	600	mW
	S.O. Package only	500	
TL	Lead Temperature (Soldering 10 seconds)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Unless otherwise specified all voltages are referenced to ground.

- 2. Power dissipation temperature derating plastic "N" package: –12 mW/°C from 65°C to 85°C.

# **MM74HC245A**

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter		Min	Max	Unit
V <sub>CC</sub>	Supply Voltage		2	6	V
V <sub>IN</sub> , V <sub>OUT</sub>	DC Input or Output Voltage		0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range		-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise/Fall Times V <sub>CC</sub> = 2.0 V		-	1000	ns
	V <sub>CC</sub> = 4.5 V		-	500	
		V <sub>CC</sub> = 6.0 V	-	400	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

# DC ELECTRICAL CHARACTERISTICS (Note 3)

				T <sub>A</sub> =	25°C	T <sub>A</sub> = −40°C to 85°C	T <sub>A</sub> = -55°C to 125°C	
Symbol	Parameter	Conditions	V <sub>CC</sub> (V)	Тур.		Guaranteed L	imits	Unit
V <sub>IH</sub>	Minimum HIGH Level		2.0	-	1.50	1.50	1.50	V
	Input Voltage		4.5	-	3.15	3.15	3.15	
			6.0	-	4.20	4.20	4.20	
V <sub>IL</sub>	Maximum LOW Level		2.0	-	0.50	0.50	0.50	V
	Input Voltage		4.5	-	1.35	1.35	1.35	
			6.0	-	1.80	1.80	1.80	
V <sub>OH</sub>	Minimum HIGH Level	$V_{IN} = V_{IH} \text{ or } V_{IL}$	2.0	2.0	1.9	1.9	1.9	V
	Output Voltage	I <sub>OUT</sub>   ≤ 20 μA	4.5	4.5	4.4	4.4	4.4	
			6.0	6.0	5.9	5.9	5.9	
		$V_{IN} = V_{IH} \text{ or } V_{IL},$ $ I_{OUT}  \le 6.0 \text{ mA}$	4.5	4.20	3.98	3.84	3.70	
		$V_{IN} = V_{IH} \text{ or } V_{IL},$ $ I_{OUT}  \le 7.8 \text{ mA}$	6.0	5.70	5.48	5.34	5.20	
V <sub>OL</sub>	Maximum LOW Level	$V_{IN} = V_{IH} \text{ or } V_{IL}$	2.0	0	0.1	0.1	0.1	V
	Output Voltage	I <sub>OUT</sub>   ≤ 20 μA	4.5	0	0.1	0.1	0.1	
			6.0	0	0.1	0.1	0.1	
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT}  \le 6.0 \text{ mA}$	4.5	0.20	0.26	0.33	0.40	
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT}  \le 7.8 \text{ mA}$	6.0	0.20	0.26	0.33	0.40	
I <sub>IN</sub>	Input Leakage Current (G and DIR)	V <sub>IN</sub> = V <sub>CC</sub> or GND	6.0	-	±0.1	±1.0	±1.0	μΑ
I <sub>OZ</sub>	Maximum 3-STATE Output Leakage Current	$V_{OUT} = V_{CC}$ or GND Enable $\overline{G} = V_{IH}$	6.0	-	±0.5	±5.0	±10	μΑ
Icc	Maximum Quiescent Supply Current	$\begin{split} &V_{IN} = V_{CC} \text{ or GND,} \\ &I_{OUT} = 0  \mu\text{A} \end{split}$	6.0	-	8.0	80	160	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product

performance is indicated in the Electrical Characteristics for the listed test conditions, thress otherwise noted. Floating performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. For a power supply of 5 V ±10% the worst case output voltages (V<sub>OH</sub>, and V<sub>OL</sub>) occur for HC at 4.5 V. Thus the 4.5 V values should be used when designing with this supply. Worst case V<sub>IH</sub> and V<sub>IL</sub> occur at V<sub>CC</sub> = 5.5 V and 4.5 V respectively. (The V<sub>IH</sub> value at 5.5 V is 3.85 V.) The worst case leakage current (I<sub>IN</sub>, I<sub>CC</sub>, and I<sub>OZ</sub>) occur for CMOS at the higher voltage and so the 6.0 V values should be used.

# **MM74HC245A**

#### **AC ELECTRICAL CHARACTERISTICS**

 $(V_{CC} = 5 \text{ V}, T_A = 25^{\circ}\text{C}, t_r = t_f = 6 \text{ ns})$ 

Symbol	Parameter	Conditions	Тур.	Guaranteed Limit	Unit
t <sub>PHL</sub> , t <sub>PLH</sub>	Maximum Propagation Delay	C <sub>L</sub> = 45 pF	12	17	ns
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Output Enable Time	$R_L = 1 \text{ k}\Omega$ , $C_L = 45 \text{ pF}$	24	35	ns
$t_{PLZ},t_{PHZ}$	Maximum Output Disable Time	$R_L = 1 \text{ k}\Omega, C_L = 5 \text{ pF}$	18	25	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# **AC ELECTRICAL CHARACTERISTICS**

(V<sub>CC</sub> = 2.0 V to 6.0 V,  $C_L$  = 50 pF,  $t_r$  =  $t_f$  = 6 ns, unless otherwise specified)

				T <sub>A</sub> =	25°C	T <sub>A</sub> = -40°C to 85°C	T <sub>A</sub> = -55°C to 125°C	
Symbol	Parameter	Conditions	V <sub>CC</sub> (V)	Тур.		Guaranteed L	imits	Unit
t <sub>PHL</sub> , t <sub>PLH</sub>	Maximum Propagation Delay	$C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	2.0	31 41	90 96	113 116	135 128	ns
		C <sub>L</sub> = 50 pF C <sub>L</sub> = 150 pF	4.5	13 17	18 22	23 28	27 33	
		C <sub>L</sub> = 50 pF C <sub>L</sub> = 150 pF	6.0	11 14	15 19	19 23	23 28	
t <sub>PZH</sub> , t <sub>PZL</sub>	Maximum Output Enable Time	$R_L = 1 \text{ k}\Omega$ $C_L = 50 \text{ pF}$ $C_L = 150 \text{ pF}$	2.0	71 81	190 240	240 300	285 360	ns
		C <sub>L</sub> = 50 pF C <sub>L</sub> = 150 pF	4.5	26 31	38 48	48 60	57 72	
		C <sub>L</sub> = 50 pF C <sub>L</sub> = 150 pF	6.0	21 25	32 41	41 51	48 61	
$t_{PHZ},t_{PLZ}$	Maximum Output Disable	R <sub>L</sub> = 1 kΩ	2.0	39	135	169	203	ns
	Time	C <sub>L</sub> = 50 pF	4.5	20	27	34	41	1
			6.0	18	23	29	34	1
t <sub>TLH</sub> , t <sub>THL</sub>	Output Rise and Fall Time	C <sub>L</sub> = 50 pF	2.0	20	60	75	90	ns
			4.5	6	12	15	18	1
			6.0	5	10	13	15	1
C <sub>PD</sub>	Power Dissipation Capacitance (Note 4)	G = V <sub>IL</sub> G = V <sub>IH</sub>		50 5	-	-	-	pF
C <sub>IN</sub>	Maximum Input Capacitance			5	10	10	10	pF
C <sub>IN/OUT</sub>	Maximum Input/Output Capacitance, A or B			15	20	20	20	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product

performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. C<sub>PD</sub> determines the no load dynamic power consumption, P<sub>D</sub> = C<sub>PD</sub> V<sub>CC</sub><sup>2</sup> f + I<sub>CC</sub> V<sub>CC</sub>, and the no load dynamic current consumption, I<sub>S</sub> = C<sub>PD</sub> V<sub>CC</sub> f + I<sub>CC</sub>.

# **MM74HC245A**

# **ORDERING INFORMATION**

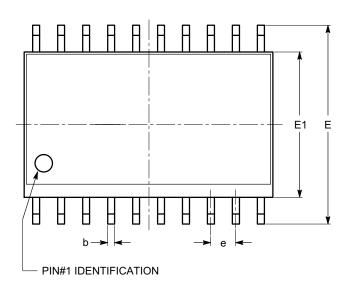
Device	Package	Shipping <sup>†</sup>
MM74HC245AWM	SOIC-20 WB (Pb-Free)	38 Units / Tube
MM74HC245AWMX	SOIC-20 (Pb-Free)	1000 / Tape & Reel
MM74HC245AMTC	TSSOP-20 WB (Pb-Free)	75 Units / Tube
MM74HC245AMTCX	TSSOP-20 (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



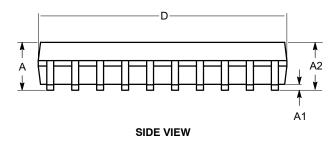
SOIC-20, 300 mils CASE 751BJ-01 ISSUE O

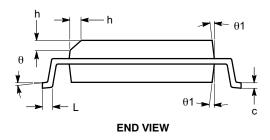
**DATE 19 DEC 2008** 



SYMBOL	MIN	NOM	MAX
А	2.36	2.49	2.64
A1	0.10		0.30
A2	2.05		2.55
b	0.31	0.41	0.51
С	0.20	0.27	0.33
D	12.60	12.80	13.00
E	10.01	10.30	10.64
E1	7.40	7.50	7.60
е		1.27 BSC	
h	0.25		0.75
L	0.40	0.81	1.27
θ	0°		8°
θ1	5°		15°

**TOP VIEW** 





#### Notes:

- (1) All dimensions are in millimeters. Angles in degrees.
- (2) Complies with JEDEC MS-013.

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DESCRIPTION:	SOIC-20, 300 MILS		PAGE 1 OF 1

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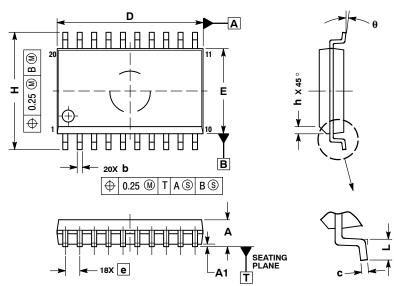




SOIC-20 WB CASE 751D-05 **ISSUE H** 

**DATE 22 APR 2015** 

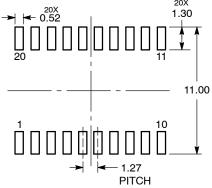
#### SCALE 1:1



- DIMENSIONS ARE IN MILLIMETERS.
   INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- PROTRUSION.
  MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
b	0.35	0.49		
С	0.23	0.32		
D	12.65	12.95		
E	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
A	0 °	7 °		

#### **RECOMMENDED SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

# **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



# TSSOP-20 WB CASE 948E ISSUE D

**DATE 17 FEB 2016** 





#### NOTES:

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
- (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

  7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252	BSC
M	0°	8°	0°	8°

#### **SOLDERING FOOTPRINT**



# **GENERIC MARKING DIAGRAM\***



= Assembly Location

= Wafer Lot

= Year

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

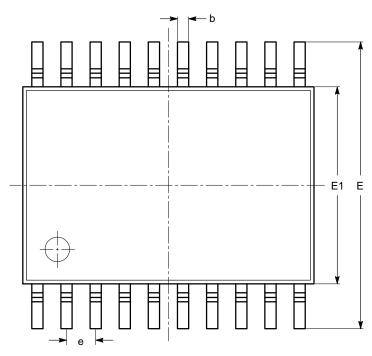
\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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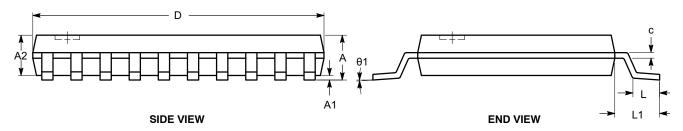
**TSSOP20, 4.4x6.5** CASE 948AQ-01 ISSUE A

**DATE 19 MAR 2009** 



SYMBOL	MIN	NOM	MAX
Α			1.20
A1	0.05		0.15
A2	0.80		1.05
b	0.19		0.30
С	0.09		0.20
D	6.40	6.50	6.60
E	6.30	6.40	6.50
E1	4.30	4.40	4.50
е		0.65 BSC	
L	0.45	0.60	0.75
L1		1.00 REF	
θ	0°		8°

**TOP VIEW** 



#### Notes:

- (1) All dimensions are in millimeters. Angles in degrees.
- (2) Complies with JEDEC MO-153.

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DESCRIPTION:	TSSOP20, 4.4X6.5		PAGE 1 OF 1	

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